

# MTM232270LBF Silicon N-channel MOS FET

### For switching

MTM13227 in SMini3 type package

### Features

- Low drain-source On-state resistance : RDS(on) typ = 85 m $\Omega$  (VGS = 4.0 V)
- Low drive voltage: 2.5 V drive Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)
- Marking Symbol : ET

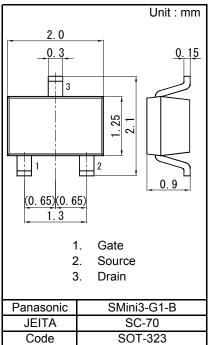
### Packaging

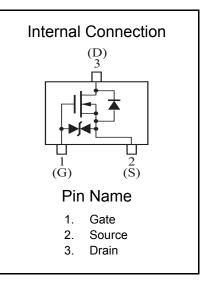
Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C						
項目	記号	定格	単位			
Drain-source Voltage	VDS	20	V			
Gate-source Voltage	VGS	±10	v			
Drain current	ID	2.0	A			
Peak drain current <sup>*1</sup>	IDp	8	A			
Power dissipation <sup>*2</sup>	PD	500	mW			
Channel temperature	Tch	150	°C			
Operating ambient temperature	Topr	-40 to +85	°C			
Storage Temperature Range	Tstg	-55 to +150	°C			
	0/					

Note) \*1 Pulse width  $\leq 10 \ \mu s$ , Duty cycle  $\leq 1 \ \%$ 

\*2 Measuring on ceramic board at  $40 \times 38 \times 0.1$  mm Absolute maximum rating PD without heat sink shall be made 150 mW.







± 3 °C					
記号	条件	最小	標準	最大	単位
VDSS	ID = 1 mA, VGS = 0 V	20			V
IDSS	VDS = 20 V, VGS = 0 V			10	μA
IGSS	VGS = ±8 V, VDS = 0 V			±10	μA
Vth	ID = 1.0 mA, VDS = 10 V	0.4	0.85	1.3	V
RDS(ON)1	ID = 1 A, VGS = 4 V		85	110	mΩ
RDS(ON)2	ID = 0.5 A, VGS = 2.5 V		100	150	
Yfs	ID = 1 A, VDS = 10 V, f = 1 kHz	3.0			S
Ciss			290		pF
Coss	VDS = 10 V, VGS = 0, f = 1 MHz		26		
Crss			20		
ton	VDD = 10 V, VGS = 0 to 4 V ID = 1 A		12		ns
toff	VDD = 10 V, VGS = -4 to 0 V ID = 1 A		60		ns
	VDSS IDSS IGSS Vth RDS(ON)1 RDS(ON)2  Yfs  Ciss Coss Crss ton	記号 条件 VDSS ID = 1 mA, VGS = 0 V IDSS VDS = 20 V, VGS = 0 V IGSS VGS = $\pm 8$ V, VDS = 0 V Vth ID = 1.0 mA, VDS = 10 V RDS(ON)1 ID = 1 A, VGS = 4 V RDS(ON)2 ID = 0.5 A, VGS = 2.5 V [Yfs] ID = 1 A, VDS = 10 V, f = 1 kHz Ciss Coss VDS = 10 V, VGS = 0, f = 1 MHz Crss ton VDD = 10 V, VGS = 0 to 4 V ID = 1 A VDD = 10 V, VGS = -4 to 0 V	記号 条件 最小   VDSS ID = 1 mA, VGS = 0 V 20   IDSS VDS = 20 V, VGS = 0 V 20   IGSS VGS = $\pm 8$ V, VDS = 0 V 0.4   Vth ID = 1 .0 mA, VDS = 10 V 0.4   RDS(ON)1 ID = 1 A, VGS = 4 V 0.4   RDS(ON)2 ID = 0.5 A, VGS = 2.5 V 0.4   IYfs ID = 1 A, VDS = 10 V, f = 1 kHz 3.0   Ciss VDS = 10 V, VGS = 0, f = 1 MHz 0.4   Crss VDD = 10 V, VGS = 0 to 4 V 0.4   ton VDD = 10 V, VGS = -4 to 0 V 0.4	記号 条件 最小 標準   VDSS ID = 1 mA, VGS = 0 V 20   IDSS VDS = 20 V, VGS = 0 V 20   IGSS VGS = $\pm 8$ V, VDS = 0 V 04   Vth ID = 1.0 mA, VDS = 10 V 0.4   Vth ID = 1 A, VGS = 4 V 85   RDS(ON)1 ID = 1 A, VGS = 2.5 V 100   IYfs ID = 1 A, VDS = 10 V, f = 1 kHz 3.0   Ciss VDS = 10 V, VGS = 0, f = 1 MHz 26   Crss VDD = 10 V, VGS = 0 to 4 V 12   ton VDD = 10 V, VGS = -4 to 0 V 60	記号 条件 最小 標準 最大   VDSS ID = 1 mA, VGS = 0 V 20 10   IDSS VDS = 20 V, VGS = 0 V 10   IGSS VGS = $\pm 8$ V, VDS = 0 V $\pm 10$ Vth ID = 1.0 mA, VDS = 10 V 0.4 0.85 1.3   RDS(ON)1 ID = 1 A, VGS = 4 V 85 110   RDS(ON)2 ID = 0.5 A, VGS = 2.5 V 100 150   IYfs ID = 1 A, VDS = 10 V, f = 1 kHz 3.0 290   Coss VDS = 10 V, VGS = 0, f = 1 MHz 26 20   ton VDD = 10 V, VGS = 0 to 4 V 12 12   toff VDD = 10 V, VGS = -4 to 0 V 60 60

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

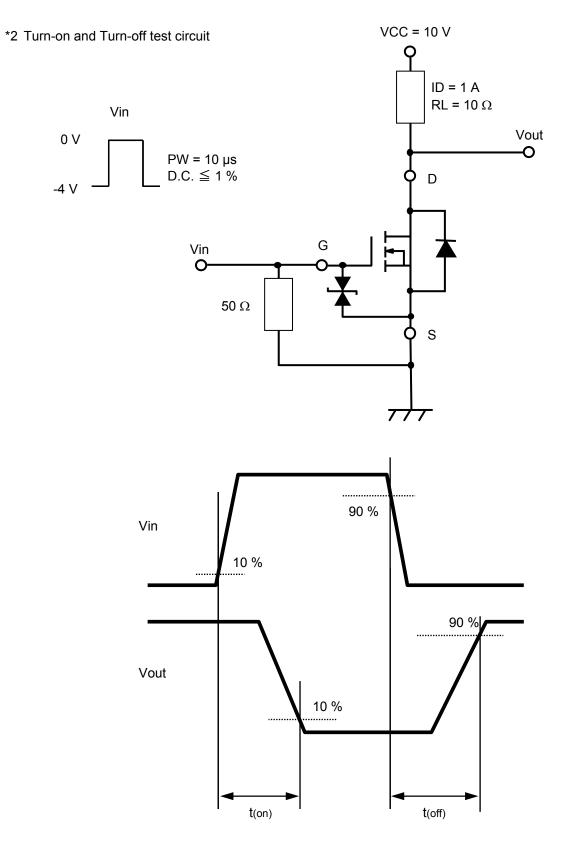
2. \*1 Pulse test : Pulse width  $\leq$  10  $\mu s$  , Duty cycle  $\leq$  1 %

\*2 Turn-on and Turn-off test circuit

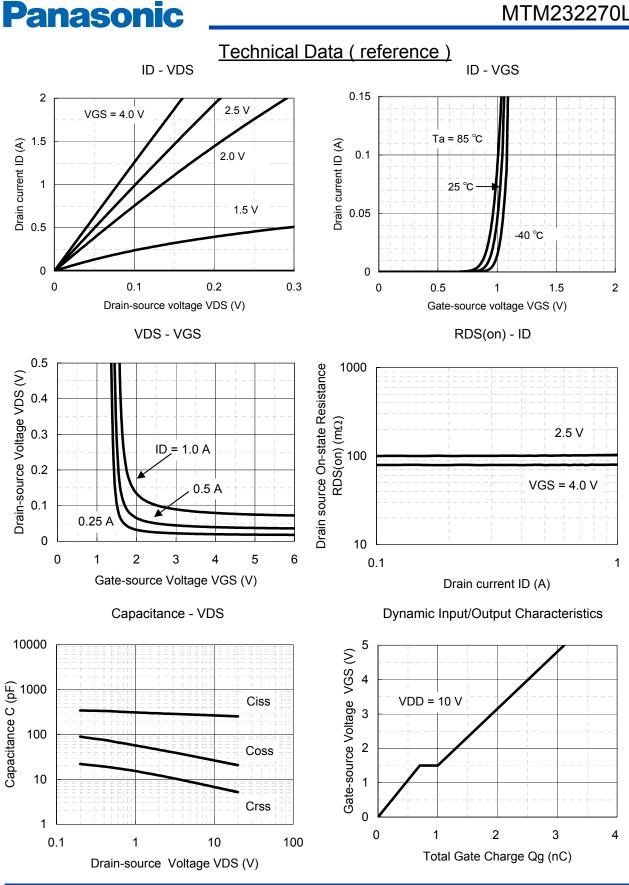
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# Panasonic

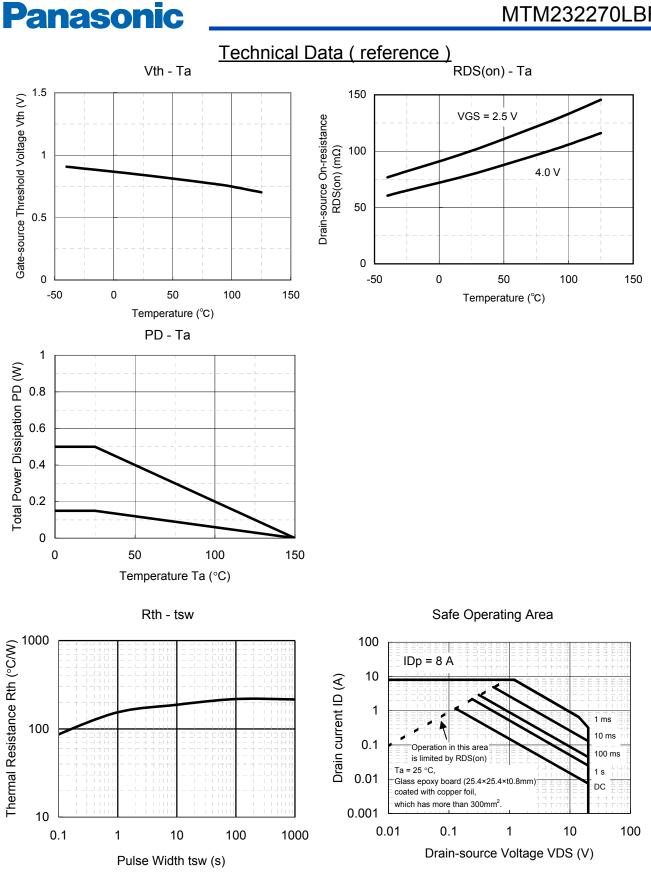
MOS FET MTM232270LBF



Established : 2011-03-09 Revised : 2013-09-02



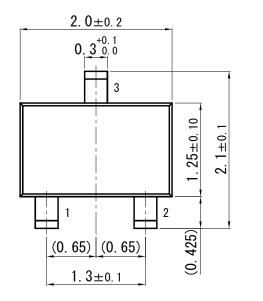
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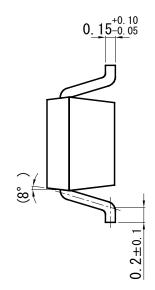


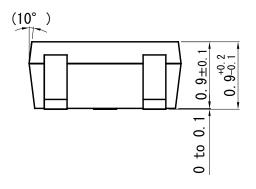
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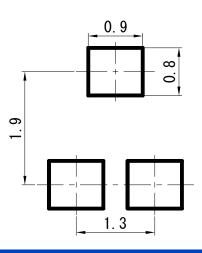
# SMini3-G1-B







Land Pattern (Reference) (Unit : mm)



Established : 2011-03-09 Revised : 2013-09-02

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